

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

3DL41A

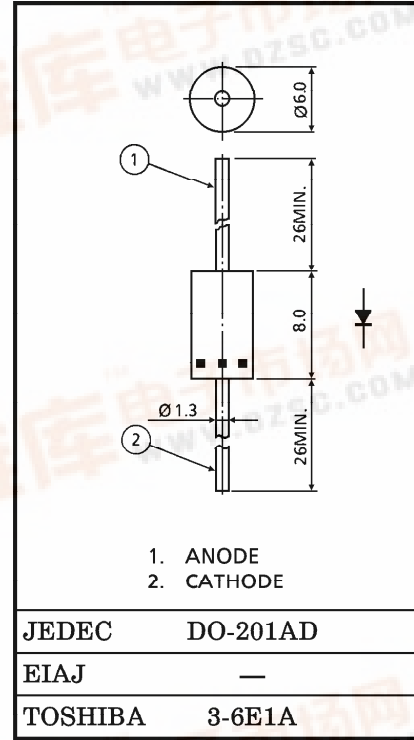
SWITCHING TYPE POWER SUPPLY APPLICATIONS

Unit in mm

- Repetitive Peak Reverse Voltage : $V_{RRM}=200V$
- Average Forward Current : $I_F(AV)=3.0A$
- Very Fast Reverse-Recovery Time : $t_{rr}=35ns$ (Max.)
- Low Forward Voltage : $V_{FM}=0.98V$ (Max.)
- Available to Raduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Average Forward Current	$I_F(AV)$	3.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	80 (50Hz)	A
		88 (60Hz)	
Junction Temperature	T_j	-40~150	°C
Storage Temperature	T_{stg}	-40~150	°C

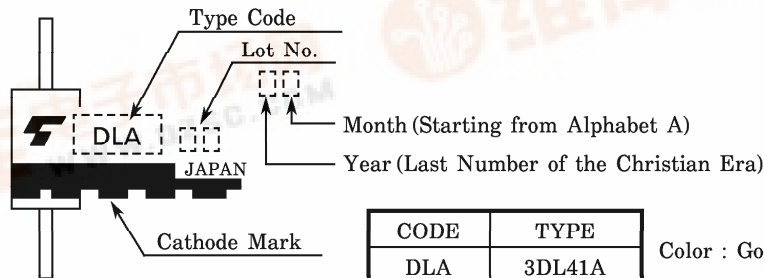


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Weight : 1.18g

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM}=3.0A$	—	—	0.98	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM}=200V$	—	—	100	μA
Reverse Recovery Time	t_{rr}	$I_F=1A, di/dt=-30A/\mu s$	—	—	35	ns
Forward Recovery Time	t_{fr}	$I_F=1.0A$	—	—	100	ns
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	—	—	57	°C/W
Thermal Resistance	$R_{th(j-l)}$	Junction to Lead	—	—	18	°C/W

MARKING



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TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

